★ Green Device
★ Super Low Gate
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology
★ 100% EAS Guaranteed

Product Summary

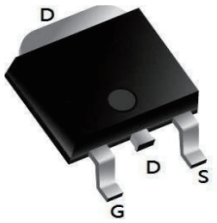
RoHS

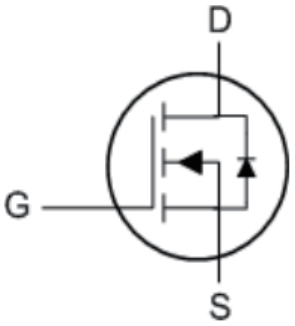
BVDSS	RDSON	ID
60V	23mΩ	30A

Description

The 30N06 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and and gate charge for most of the synchronous buck converter applications. The 30N06 meets the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Typ.	Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	30	A
		T_C = 100℃	13	A
I_{DM}	Pulsed Drain Current note1		100	A
EAS	Single Pulsed Avalanche Energy note2		39	mJ
P_D	Power Dissipation	T_C = 25℃	41.7	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		50	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

Electrical Characteristics (T_J =25 °C unless otherwise specified)

Symbol	Parameter		Test condition	Min.	Typ.	Max.	Units
Static Characteristics							
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		V_{GS} = 0V, I_D = 250μA	60	-	-	V
I_{GSS}	Gate-Body Leakage Current		V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	T_J=25°C	V_{DS} = 60V, V_{GS} = 0V	-	-	1	μA
		T_J=100°C		-	-	100	
$V_{GS(th)}$	Gate-Threshold Voltage		V_{DS} = V_{GS}, I_D = 250μA	1.2	1.7	2.5	V
$R_{DS(on)}$	Drain-Source on-Resistance[4]		V_{GS} = 10V, I_D = 10A	-	23	32	mΩ
			V_{GS} = 4.5V, I_D = 5A	-	31.5	40	
g_{fs}	Forward Transconductance[4]		V_{DS} = 5V, I_D = 10A	-	15.5	-	S
Dynamic Characteristics[5]							
C_{iss}	Input Capacitance		V_{DS} = 30V, V_{GS} =0V, f =1MHz	-	1355	-	pF
C_{oss}	Output Capacitance			-	60	-	
C_{rss}	Reverse Transfer Capacitance			-	49	-	
R_G	Gate Resistance		f =1MHz	-	1.2	-	Ω
Switching Characteristics[5]							
Q_g	Total Gate Charge		V_{GS} = 10V, V_{DD} = 30V, I_D= 10A	-	22	-	nC
Q_{gs}	Gate-Source Charge			-	4.2	-	
Q_{gd}	Gate-Drain Charge			-	6.9	-	
$t_{d(on)}$	Turn-on Delay Time		V_{GS} =10V, V_{DD} = 30V, R_G = 3Ω, I_D= 10A	-	6.4	-	ns
t_r	Rise Time			-	15.3	-	
$t_{d(off)}$	Turn-off Delay Time			-	25	-	
t_f	Fall Time			-	7.6	-	
t_{rr}	Body Diode Reverse Recovery Time		I_F=10A, dI_F/dt=100A/μs	-	26	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge			-	45	-	nC
Drain-Source Body Diode Characteristics							
V_{SD}	Diode Forward Voltage[4]		I_S = 10A, V_{GS} = 0V	-	-	1.2	V
I_S	Continuous Source Current	T_C=25°C	-	-	-	30	A

Notes:
1.Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C
2.The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.4mH, IAS=14A
3.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5.This value is guaranteed by design hence it is not included in the production test.

Typical Electrical and Thermal Characteristics (Curves)

Figure1: Output Characteristics

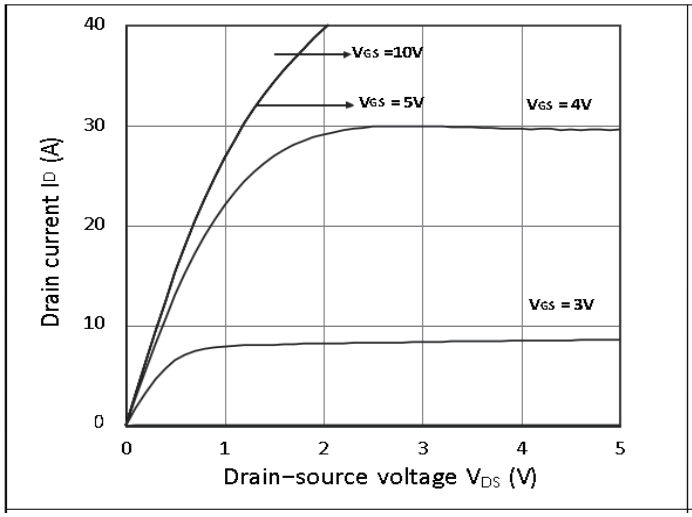


Figure 2: Transfer Characteristics

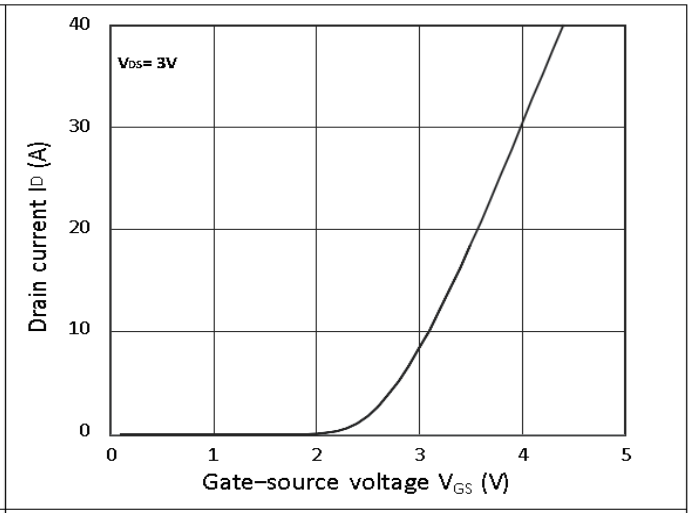


Figure 3:Forward Characteristics of Rever

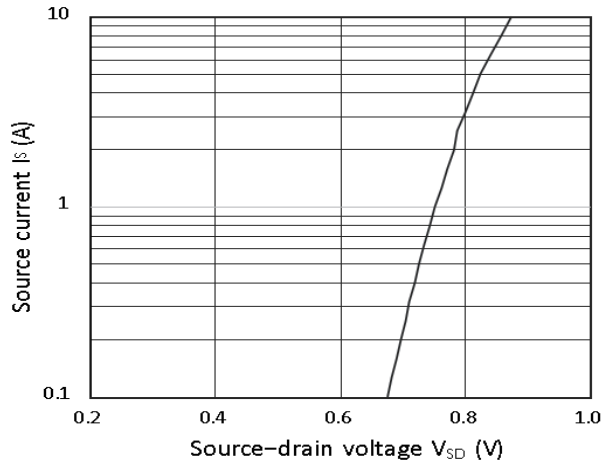


Figure 4: RDS(ON) vs. VGS

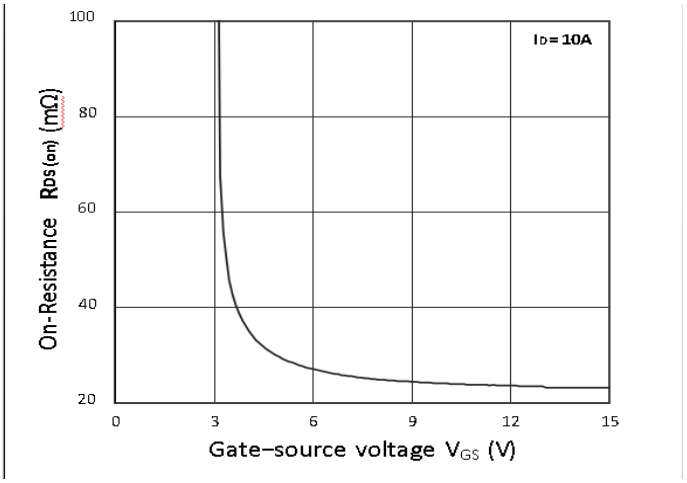


Figure 5: RDS(ON) vs. ID

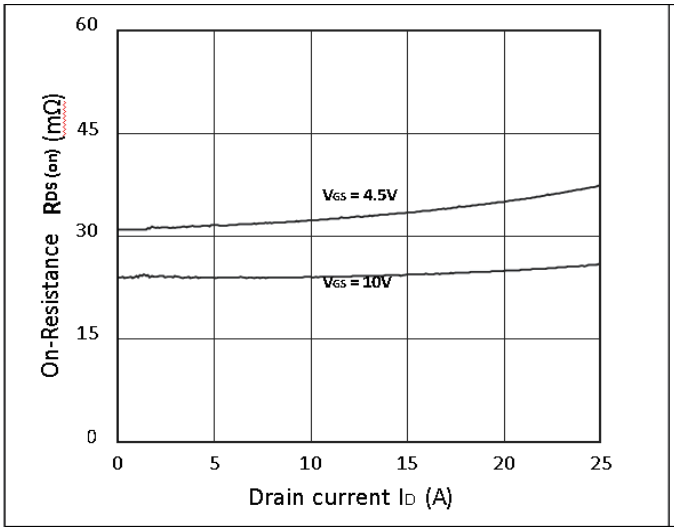
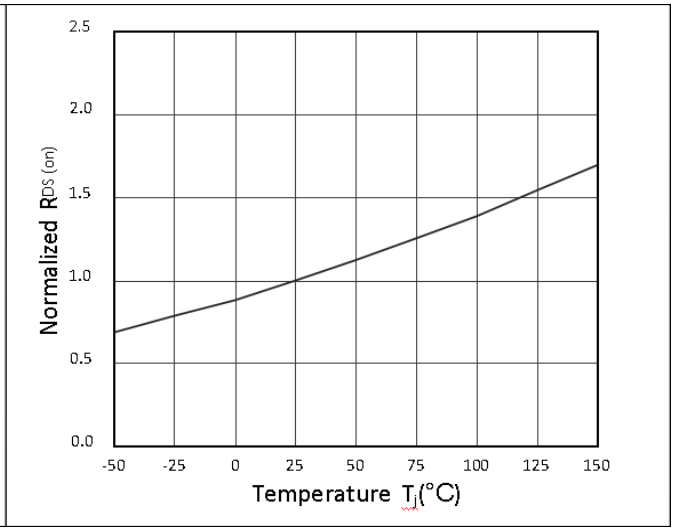


Figure 6:Normalized RDSON v.s TJ



Typical Performance Characteristics

Figure 7: Capacitance

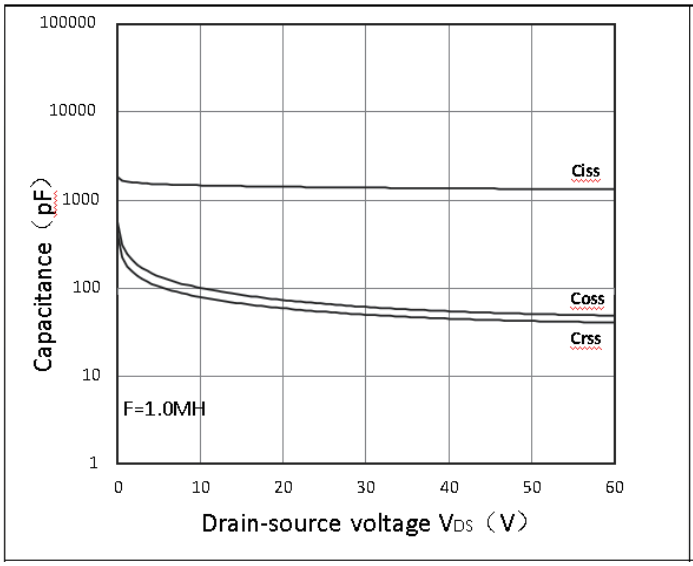


Figure 8:Gate Charge Characteristics

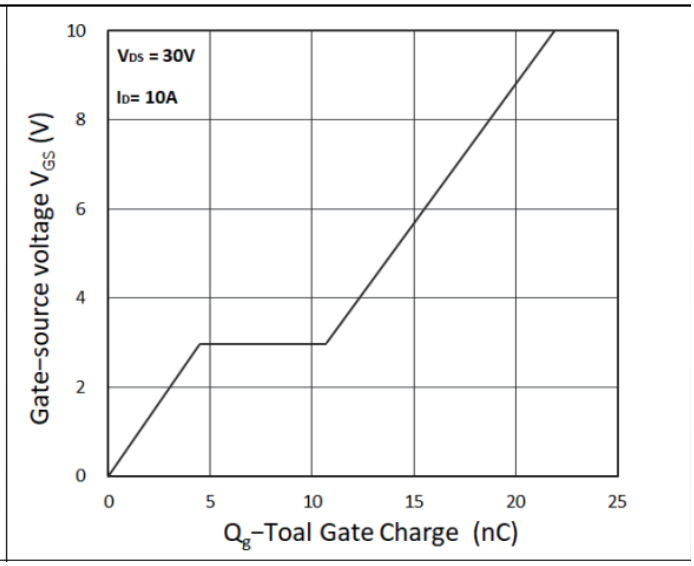


Figure 9:Normalized Maximum Transient

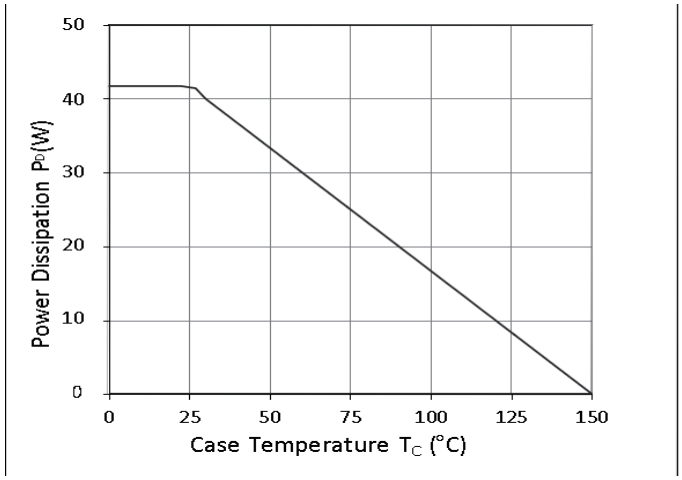


Figure 10:Safe Operating Area

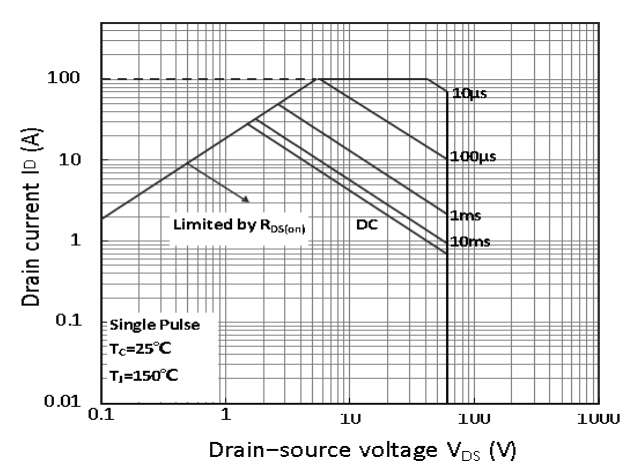
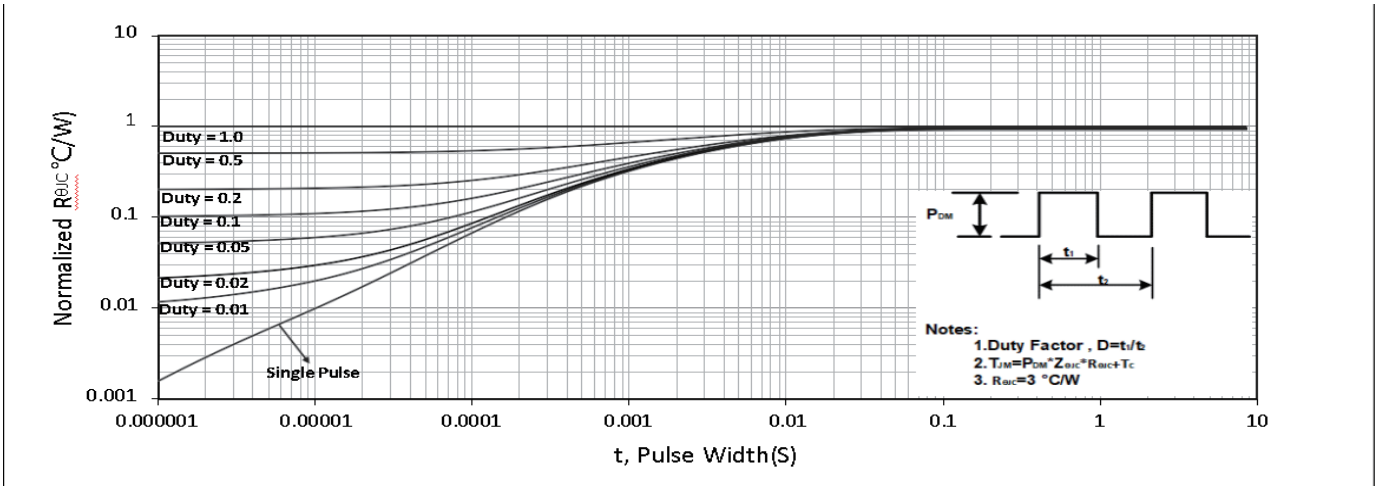
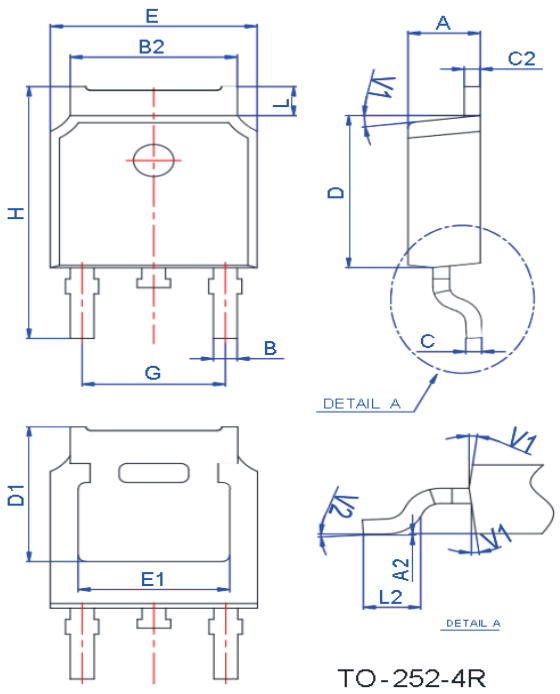


Figure 11:Normalized Maximum Transient



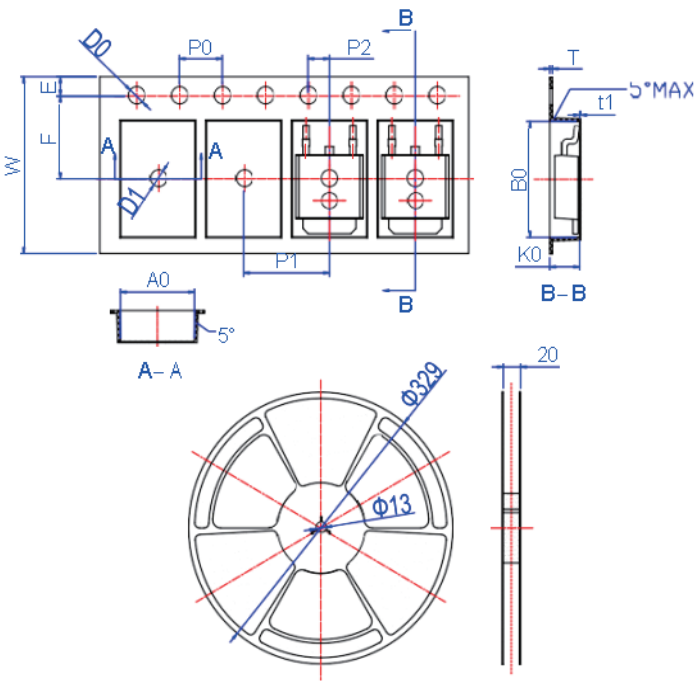
Package Mechanical Data-TO-252



TO-252-4R

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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